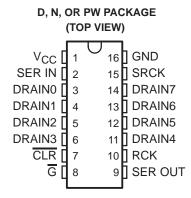
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- Low r<sub>DS(on)</sub> . . . 7 Ω Typ
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS Transistor Outputs of 100-mA Continuous Current
- 250-mA Current Limit Capability
- ESD Protection . . . 2500 V
- Output Clamp Voltage . . . 33 V
- Devices Are Cascadable
- Low Power Consumption

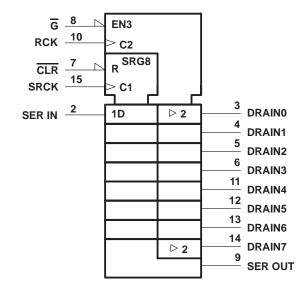
#### description

The TPIC6C595 is a monolithic, medium-voltage, low-current power 8-bit shift register designed for use in systems that require relatively moderate load power such as LEDs. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other low-current or medium-voltage loads.

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift register clock (SRCK) and the register clock (RCK), respectively. The device transfers data out the serial output (SER OUT) port on the rising edge of SRCK. The storage register transfers data to the output buffer when shift register clear (CLR) is high. When CLR is low, the input shift register is cleared. When output enable (G) is held high, all data in the output buffers is held low and all drain



#### logic symbol†



<sup>&</sup>lt;sup>†</sup>This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

outputs are off. When  $\overline{G}$  is held low, data from the storage register is transparent to the output buffers. When data in the output buffers is low, the DMOS transistor outputs are off. When data is high, the DMOS transistor outputs have sink-current capability. The SER OUT allows for cascading of the data from the shift register to additional devices.



This device contains circuits to protect its inputs and outputs against damage due to high static voltages or electrostatic fields. These circuits have been qualified to protect this device against electrostatic discharges (ESD) of up to 2 kV according to MIL-STD-883C, Method 3015; however, it is advised that precautions be taken to avoid application of any voltage higher than maximum-rated voltages to these high-impedance circuits. During storage or handling, the device leads should be shorted together or the device should be placed in conductive foam. In a circuit, unused inputs should always be connected to an appropriated logic voltage level, preferably either V<sub>CC</sub> or ground. Specific guidelines for handling devices of this type are contained in the publication *Guidelines for Handling Electrostatic-Discharge-Sensitive (ESDS) Devices and Assemblies* available from Texas Instruments.



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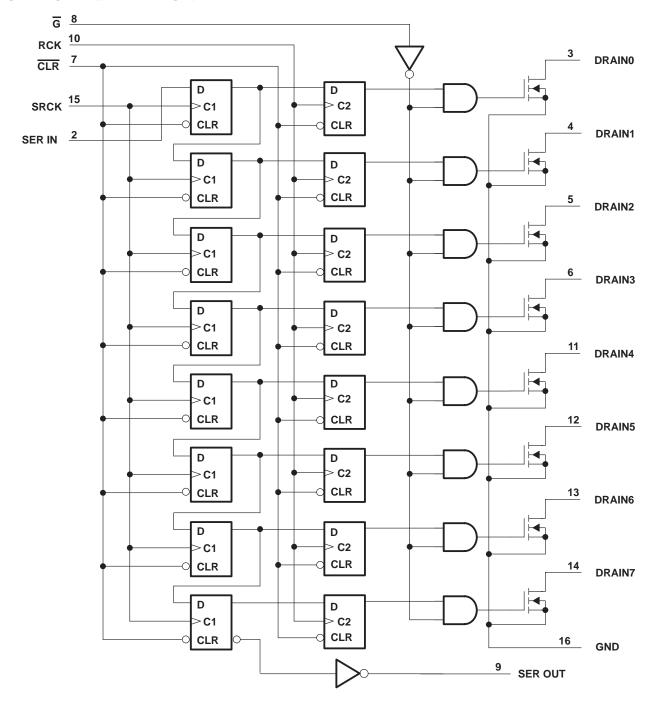
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#### description (continued)

Outputs are low-side, open-drain DMOS transistors with output ratings of 33 V and 100 mA continuous sink-current capability. Each output provides a 250-mA maximum current limit at  $T_C$  = 25°C. The current limit decreases as the junction temperature increases for additional device protection. The device also provides up to 2500 V of ESD protection when tested using the human-body model and the 200-V machine model.

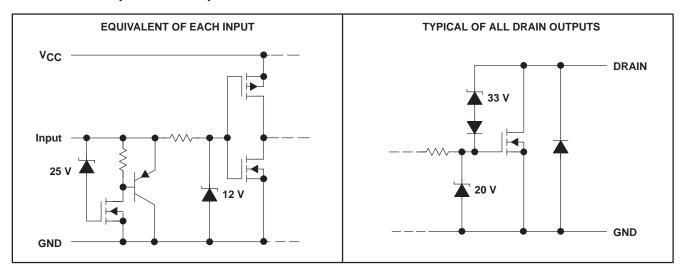
The TPIC6C595 is characterized for operation over the operating case temperature range of -40°C to 125°C.

#### logic diagram (positive logic)





#### schematic of inputs and outputs



# absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) $^{\dagger}$

Logic supply voltage, V <sub>CC</sub> (see Note 1)	7 V
Logic input voltage range, V <sub>I</sub>	
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	
Pulsed drain current, each output, all outputs on, I <sub>D</sub> , T <sub>C</sub> = 25°C (see Note 3)	
Continuous drain current, each output, all outputs on, $I_D$ , $T_C = 25^{\circ}C$	
Peak drain current single output, I <sub>DM</sub> ,T <sub>C</sub> = 25°C (see Note 3)	
Single-pulse avalanche energy, E <sub>AS</sub> (see Figure 4)	
Avalanche current, I <sub>AS</sub> (see Note 4)	
Continuous total dissipation	
Operating virtual junction temperature range, T <sub>J</sub>	
Operating case temperature range, T <sub>C</sub>	40°C to 125°C
Storage temperature range, T <sub>stg</sub>	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
  - 2. Each power DMOS source is internally connected to GND.
  - 3. Pulse duration  $\leq$  100  $\mu$ s and duty cycle  $\leq$  2%.
  - 4. DRAIN supply voltage = 15 V, starting junction temperature ( $T_{JS}$ ) = 25°C, L = 1.5 H,  $I_{AS}$  = 200 mA (see Figure 4).

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>C</sub> = 25°C	T <sub>C</sub> = 125°C POWER RATING
D	1087 mW	8.7 mW/°C	217 mW
N	1470 mW	11.7 mW/°C	294 mW
PW	1372 mW	10.976 mW/°C	274 mW



## TPIC6C595 POWER LOGIC 8-BIT SHIFT REGISTER

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#### recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5.5	V
High-level input voltage, V <sub>IH</sub>	0.85 V <sub>CC</sub>		V
Low-level input voltage, V <sub>IL</sub>		0.15 V <sub>CC</sub>	V
Pulsed drain output current, $T_C = 25$ °C, $V_{CC} = 5$ V, all outputs on (see Notes 3 and 5 and Figure 11)		250	mA
Setup time, SER IN high before SRCK↑, t <sub>SU</sub> (see Figure 2)	20		ns
Hold time, SER IN high after SRCK↑, th (see Figure 2)	20		ns
Pulse duration, t <sub>W</sub> (see Figure 2)	40		ns
Operating case temperature, T <sub>C</sub>	-40	125	°C

## electrical characteristics, $V_{CC}$ = 5 V, $T_{C}$ = 25°C (unless otherwise noted)

	PARAMETER	TEST	MIN	TYP	MAX	UNIT	
V <sub>(BR)DSX</sub>	Drain-to-source breakdown voltage	$I_D = 1 \text{ mA}$		33	37		V
V <sub>SD</sub>	Source-to-drain diode forward voltage	IF = 100 mA			0.85	1.2	V
V <sub>OH</sub> High-level output voltage, SER OUT	High level output valtage CED OUT	$I_{OH} = -20 \mu A$ ,	V <sub>CC</sub> = 4.5 V	4.4	4.49		\/
	High-level output voltage, SER OUT	$I_{OH} = -4 \text{ mA},$	$V_{CC} = 4.5 V$	4	4.2		V
V <sub>OL</sub> Low-level output voltage, SER OUT		$I_{OL} = 20 \mu A$ ,	V <sub>CC</sub> = 4.5 V		0.005	0.1	
		$I_{OL} = 4 \text{ mA},$	V <sub>CC</sub> = 4.5 V		0.3	0.5	V
liH	High-level input current	$V_{CC} = 5.5 V$ ,	$V_I = V_{CC}$			1	μΑ
I <sub>IL</sub>	Low-level input current	$V_{CC} = 5.5 \text{ V},$	V <sub>I</sub> = 0			-1	μΑ



## switching characteristics, $V_{CC} = 5 \text{ V}$ , $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output from $\overline{G}$			80		ns
tPHL	Propagation delay time, high-to-low-level output from $\overline{G}$	]		50		ns
tpd	Propagation delay time, SRCK to SEROUT	C <sub>L</sub> = 30 pF, I <sub>D</sub> = 75 mA, See Figures 1, 2, and 9		20		ns
t <sub>r</sub>	Rise time, drain output			100		ns
t <sub>f</sub>	Fall time, drain output			80		ns
ta	Reverse-recovery-current rise time	$I_F = 100 \text{ mA}, \qquad \text{di/dt} = 10 \text{ A/}\mu\text{s},$		100		
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 3		120		ns

NOTES: 5. Technique should limit  $T_J - T_C$  to 10°C maximum.

#### thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
		D package			115	
$R_{\theta JA}$	R <sub>θ</sub> JA Thermal resistance, junction-to-ambient	N package	All 8 outputs with equal power		85	°C/W
		PW package			108	

#### PARAMETER MEASUREMENT INFORMATION 5 V **SRCK** ID. CLR 5 V $R_L = 200 \Omega$ 15 0 V SRCK 3-6, 5 V DUT **SER IN** 11 –14 Word 0 V DRAIN SER IN Generator 5 V (see Note A) 10 $C_L = 30 pF$ **RCK** (see Note B) 8 G CLR 0 V **GND** 15 V DRAIN1 0.5 V **VOLTAGE WAVEFORMS TEST CIRCUIT**

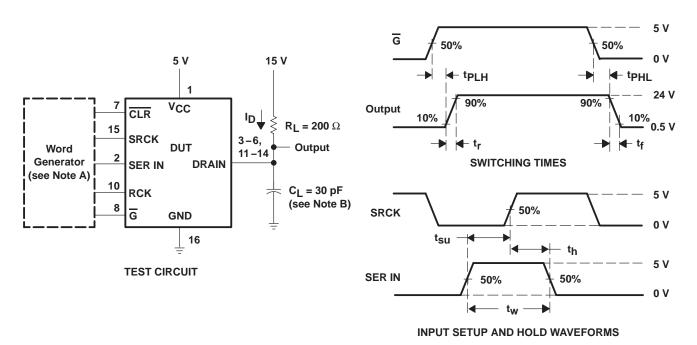
NOTES: A. The word generator has the following characteristics:  $t_{\Gamma} \le 10$  ns,  $t_{\tilde{\Gamma}} \le 10$  ns,  $t_{W} = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_{\tilde{\Omega}} = 50~\Omega$ .

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

<sup>6.</sup> These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

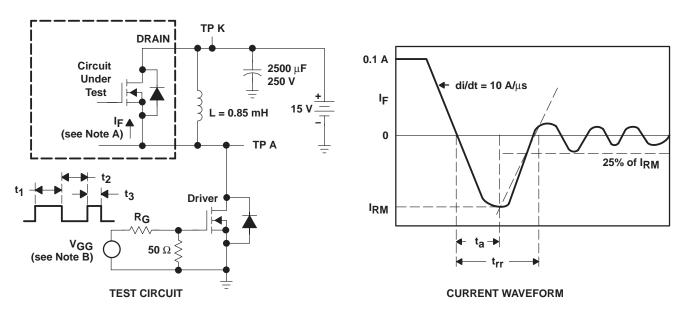
#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. The word generator has the following characteristics:  $t_{\Gamma} \le 10$  ns,  $t_{W} = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_{O} = 50~\Omega$ .

B. CL includes probe and jig capacitance.

Figure 2. Test Circuit, Switching Times, and Voltage Waveforms



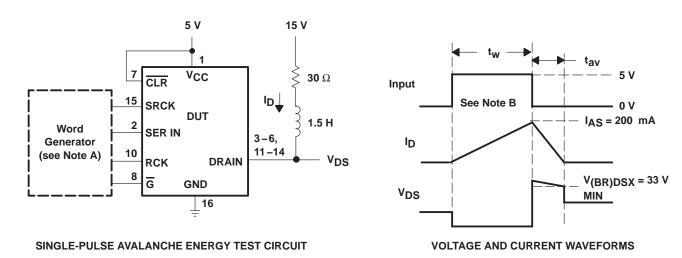
NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

B. The V<sub>GG</sub> amplitude and R<sub>G</sub> are adjusted for di/dt = 10 A/ $\mu$ s. A V<sub>GG</sub> double-pulse train is used to set I<sub>F</sub> = 0.1 A, where t<sub>1</sub> = 10  $\mu$ s, t<sub>2</sub> = 7  $\mu$ s, and t<sub>3</sub> = 3  $\mu$ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



#### PARAMETER MEASUREMENT INFORMATION

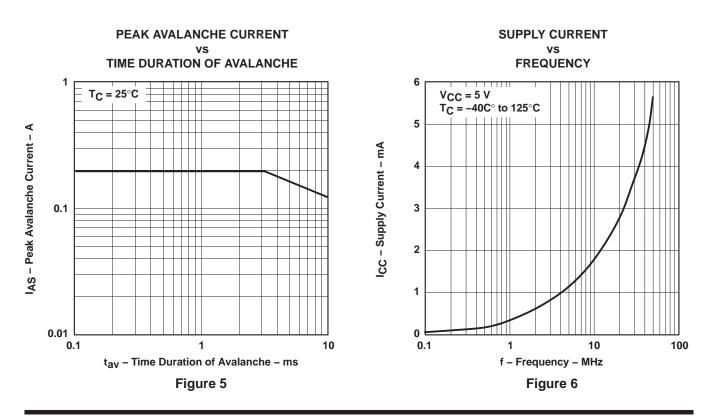


NOTES: A. The word generator has the following characteristics:  $t_f \le 10$  ns,  $t_f \le 10$  ns,  $Z_O = 50 \Omega$ .

B. Input pulse duration,  $t_W$ , is increased until peak current  $I_{AS} = 200$  mA. Energy test level is defined as  $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$  mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

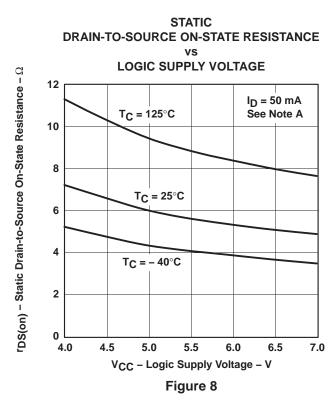
#### **TYPICAL CHARACTERISTICS**



#### **TYPICAL CHARACTERISTICS**

**DRAIN-TO-SOURCE ON-STATE RESISTANCE DRAIN CURRENT** rDS(on) – Drain-to-Source On-State Resistance –  $\Omega$ 30  $V_{CC} = 5 V$ See Note A 25 T<sub>C</sub> = 125°C 20 15 10  $T_C = 25^{\circ}C$ 5  $T_C = -40^{\circ}C$ 70 130 150 190 250 50 110 170 ID - Drain Current - mA

Figure 7



#### **SWITCHING TIME CASE TEMPERATURE** 140 $I_D = 75 \text{ mA}$ See Note A tr 120 tf 100 Switching Time - ns 80 <sup>t</sup>PLH 60 <sup>t</sup>PHL 40 20 0 -25 125 -50 100 T<sub>C</sub> - Case Temperature - °C Figure 9

NOTE A: Technique should limit  $T_J - T_C$  to 10°C maximum.



#### THERMAL INFORMATION

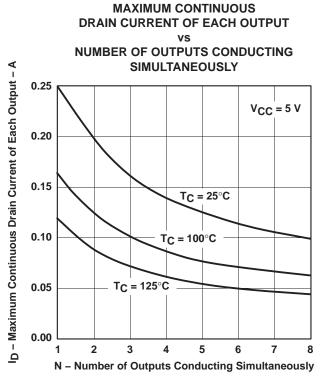


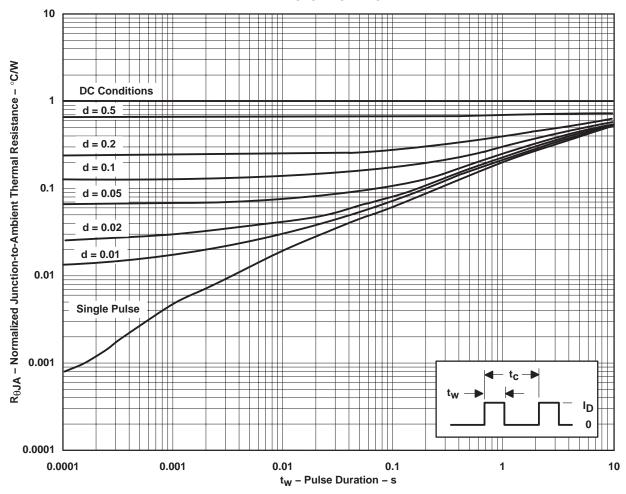
Figure 10

#### **MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT** NUMBER OF OUTPUTS CONDUCTING **SIMULTANEOUSLY** ID - Maximum Peak Drain Current of Each Output - A 0.30 d = 10%0.25 d = 20%0.20 d = 50%0.15 d = 80%0.10 $V_{CC} = 5 V$ 0.05 T<sub>C</sub> = 25°C $d = t_W/t_{period}$ = 1 ms/t<sub>period</sub> 0.00 2 4 5 6 7 3 8 N - Number of Outputs Conducting Simultaneously

Figure 11

#### THERMAL INFORMATION

# D PACKAGE<sup>†</sup> NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE vs PULSE DURATION



† Device mounted on FR4 printed-circuit board with no heat sink

 $\begin{aligned} \text{NOTES:} \quad Z_{\theta A}(t) &= r(t) \; R_{\theta JA} \\ t_W &= \text{pulse duration} \\ t_C &= \text{cycle time} \\ d &= \text{duty cycle} = t_W/t_C \end{aligned}$ 

Figure 12







7-May-2008

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPIC6C595D	ACTIVE	SOIC	D	16	40	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6C595DG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6C595DR	ACTIVE	SOIC	D	16	2500	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6C595DRG4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6C595N	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TPIC6C595PW	ACTIVE	TSSOP	PW	16	90	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6C595PWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6C595PWR	ACTIVE	TSSOP	PW	16	2000	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6C595PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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#### PW (R-PDSO-G\*\*)

#### 14 PINS SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

## D (R-PDSO-G16)

#### PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AC.



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## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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